

Туре Function

Structure

Product series White LED driver for TFT back light

BD8113EFV

Integrated buck-boost current-mode DC/DC controller

Built-in OSC (external R), External synchronous mode

- •Two integrated LED current driver channel
- (Set by a standard external R current.)
- •PWM light modulation
- FAIL output (self-diagnosis function)
- •Built-in over-voltage protection circuit (OVP) •Built-in thermal shut down circuit (TSD)

•Built-in under-voltage lock out circuit (UVLO)

- •Built-in over-current protection circuit (OCP)
- •Built-in short detection circuit (SCP)
- •Oscillation frequency accuracy $\pm 5\%$
- ·Built-in LED open short detection circuit

●Absolute maximum ratings(Ta=25°C)

Parameter	Symbol	Limits	Unit
Power supply voltage	Vcc	36	V
BOOT terminal voltage	V _{BOOT}	41	V
SW,CS,OUTH terminal voltage	V _{sw} , V _{CS} , V _{OUTH}	36	V
Between BOOT-SW terminal voltage	V _{BOOT-SW}	7	V
LED1~2 output voltage	VLED1~2	36	V
VREG,OVP,OUTL,FAIL1,FAIL2,LEDEN, ISET,VDAC,PWM,SS,COMP,RT,SYNC,EN terminal voltage	V _{VREG} , V _{OVP} , V _{OUTL} , V _{FAIL1} , V _{FAIL2} , V _{LEDEN} , V _{ISET} , V _{VDAC} , V _{PWM} , V _{SS} , V _{COMP} , V _{RT} , V _{SYNC} , V _{EN}	-0.3 ~ 7 < Vcc	V
Power dissipation	Pd	1.10 ^{%1}	W
Operating temperature range	Topr	-40~+105	°C
Storage temperature range	Tstg	-55~+150	°C
LED maximum output current	ILED	150 ^{%2%3}	mA

X1 IC mounted on glass epoxy board measuring 70mm × 70mm × 1.6mm, power dissipated at a rate of 8.8mw/°C at temperatures above 25°C.

%2 Dispersion figures for LED maximum output current and V_F are correlated. Please refer to data on separate sheet.

3 Amount of current per channel.

●Operating conditions (Ta=25°C)

Parameter	Symbol	Target value	Unit
Power supply voltage	Vcc	5.0~30	V
Oscillation frequency range	fosc	250~600	kHz
External synchronization frequency range **4 **5	f SYNC	fosc~600	kHz
External synchronization pulse duty range	f SDUTY	40~60	%

*4 Connect SYNC to GND or OPEN when not using external frequency synchronization.

3. To not switch between internal and external synchronization when an external synchronization signal is input to the device.



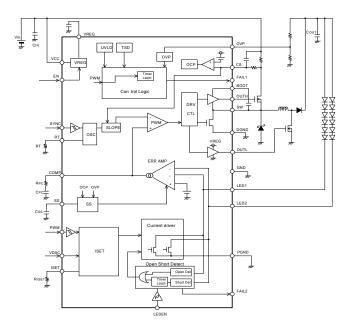
●Electrical characteristics(Unless otherwise noted VCC=12V,Ta=25°C)

			Target value	•		
Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Circuit current	Icc	-	7	14	mA	EN=Hi, SYNC=Hi, RT=OPEN PWM=Low, ISET=OPEN, CIN=10 µ F
Standby current	Isт	-	4	8	μA	EN=Low
[VREG Block]					,	
Reference voltage	VREG	4.5	5.0	5.5	V	IREG=-5mA, CREG=2.2 μ F
[OUTH Block]				<u> </u>		, ,
OUTH high-side ON resistance	Ronhh	1.5	3.5	7	Ω	Ion=-10mA
OUTH low-side ON resistance	RONHL	1.0	2.5	5.0	Ω	Ion=10mA
Over-current protection						
operating voltage	Volimit	VCC-0.66	VCC-0.6	VCC-0.54	V	
[OUTL Block]			1	11	4	
OUTL high-side ON resistance	Ronlh	2.0	4.0	8.0	Ω	Ion=-10mA
OUTL low-side ON resistance	RONLL	1.0	2.5	5.0	Ω	Ion=10mA
[SW Block]	NONEL	1.0	2.0	0.0	31	
SW low-side ON resistance	Ron sw	2.0	4.5	9.0	Ω	ION sw=10mA
[Error amplifier Block]	11011_31	2.0	т.0	0.0	ы	2014_OW TOTILA
LED voltage	VLED	0.9	1.0	1.1	V	
COMP sink current	ICOMPSINK	15	25	35	μA	VLED=2V, Vcomp=1V
		-35	-25	-15	μΑ	VLED=2V, VComp=1V VLED=0V. Vcomp=1V
COMP source current	ICOMPSOURCE	-35	-20	-15	μΑ	VLED-UV, VCOMP-IV
[Oscillating Block]		005		015		D 1001 0
Oscillating frequency	fosc	285	300	315	KHz	Rτ=100kΩ
[OVP Block]	T	r		.		T
Over-voltage detection	Vovp	1.9	2.0	2.1	V	VOVP=Sweep up
reference voltage						
OVP hysteresis width	Vohys	0.45	0.55	0.65	V	VOVP= Sweep down
SCP Latch OFF delay time	TSCP	70	100	130	ms	RT=100kΩ
[UVLO Block]			T			
UVLO voltage	Vuvlo	3.7	4.0	4.3	V	VCC : Sweep down
UVLO hysteresis width	VUHYS	400	500	600	mV	VCC : Sweep up
[LED Output Block]						
LED current relative dispersion width	ΔI LED1	-3	-	+3	%	ILED=50mA, Δ ILED1=(ILED/ ILED_AVG-1) × 100
LED current absolute dispersion width	Δ ILED2	-5	-	+5	%	ILED=50mA, Δ ILED2=(ILED/ 50mA-1) × 100
ISET voltage	VISET	1.96	2.0	2.04	V	RISET=120kΩ
PWM minimum pulse width	Tmin	25	-	-	us	FPWM=150Hz. ILED=50mA
PWM maximum duty	Dmax	-	-	100	%	FPWM=150Hz, ILED=50mA
PWM frequency	fрwм	-	-	20	KHz	Duty=50%, ILED=50mA
VDAC gain	GVDAC	_	25	-	mA/V	VDAC=0 \sim 2V ILED=VDAC \div RISET × Gain, RISET=120k Ω
LED open detection voltage	Vopen	0.2	0.3	0.4	v	ILED-VDAC - RISET × Gain, RISET-TZOK SZ VLED= Sweep down
LED open detection voltage		4.2	4.5	4.8	V	VLED- Sweep down VLED= Sweep up
0						· ·
LED short latch OFF delay time	TSHORT	70	100	130	ms	RT=100kΩ
PWM latch OFF delay time	Трум	70	100	130	ms	RT=100kΩ
[Logic Inputs (EN,SYNC,PWM,LEDEN)]	V	0.1	T			
Input High voltage	VINH	2.1	-	5.5	V	
Input Low voltage	VINL	GND	-	0.8	V	
Input current 1	In	20	35	50	μA	VIN=5V (SYNC,PWM,LEDEN)
Input current 2	Ien	15	25	35	μΑ	Ven=5V (EN)
[FAIL Output(open drain)] FAIL Low voltage	Vol	_	0.1	0.2	V	Iol=0.1mA

 $\ensuremath{\textcircled{O}}$ $\ensuremath{\textcircled{O}}$ This product is not designed for use in radioactive environments.

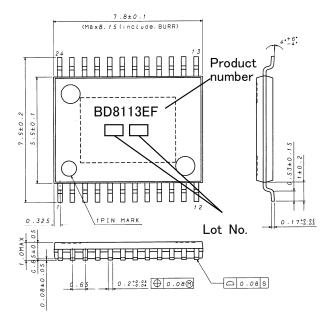


Block diagram

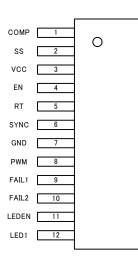


Package outlines

Pin function table



●Pin layout BD8113EFV(HTSSOP-B24)



24	VREG
23	воот
22	CS
21	OUTH
20	SW
19	DGND
18	OUTL
17	PGND
16	ISET
15	VDAC
14	OVP
13	LED2

Pin	Symbol	Function
1	COMP	ERR amplifier output
2	SS	Soft start time-setting capacitance input
3	VCC	Input power supply
4	EN	Enable input
5	RT	Oscillation frequency-setting resistance input
6	SYNC	External synchronization signal input
7	GND	Small-signal GND
8	PWM	PWM light modulation input
9	FAIL1	Failure signal output
10	FAIL2	LED open/short detection signal output
11	LEDEN	LED output enable pin
12	LED1	LED output 1
13	LED2	LED output 2
14	OVP	Over-voltage detection input
15	VDAC	DC variable light modulation input
16	ISET	LED output current-setting resistance input
17	PGND	LED output GND
18	OUTL	Low-side external MOSFET Gate Drive
19	DGND	Low-side internal MOSFET Driver Source
20	SW	High-side external MOSFET Source
21	OUTH	High-side external MOSFET Gate Drive
22	CS	DC/DC Current Sense Pin
23	BOOT	High-side MOSFET Power Supply pin
24	VREG	Internal reference voltage output



Cautions on use

1. Absolute maximum ratings

We are careful enough for quality control about this IC. So, there is no problem under normal operation, excluding that it exceeds the absolute maximum ratings. However, this IC might be destroyed when the absolute maximum ratings, such as impressed voltages or the operating temperature range(Topr), is exceeded, and whether the destruction is short circuit mode or open circuit mode cannot be specified. Please take into consideration the physical countermeasures for safety, such as fusing, if a particular mode that exceeds the absolute maximum rating is assumed.

2. Reverse polarity connection

Connecting the power line to the IC in reverse polarity (from that recommended) will damage the part. Please utilize the direction protection device as a diode in the supply line.

3. Power supply line

Due to return of regenerative current by reverse electromotive force, using electrolytic and ceramic suppress filter capacitors $(0.1 \,\mu \,\text{F})$ close to the IC power input terminals (Vcc and GND) are recommended. Please note the electrolytic capacitor value decreases at lower temperatures and examine to dispense physical measures for safety.

And, for ICs with more than one power supply, it is possible that rush current may flow instantaneously due to the internal powering sequence and delays. Therefore, give special consideration to power coupling capacitance, width of power wiring, GND wiring, and routing of wiring. Please make the power supply lines (where large current flow) wide enough to reduce the resistance of the power supply patterns, because the resistance of power supply pattern might influence the usual operation.

4. GND line

The ground line is where the lowest potential and transient voltages are connected to the IC.

5. Thermal design

Do not exceed the power dissipation (Pd) of the package specification rating under actual operation, and please design enough temperature margins.

6. Short circuit mode between terminals and wrong mounting

Do not mount the IC in the wrong direction and be careful about the reverse-connection of the power connector. Moreover, this IC might be destroyed when the dust short the terminals between them or power supply, GND.

7. Radiation

Strong electromagnetic radiation can cause operation failures.

8. ASO(Area of Safety Operation.)

Do not exceed the maximum ASO and the absolute maximum ratings of the output driver.

9. TSD(Thermal shut-down)

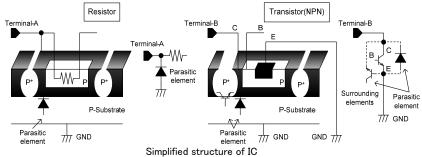
The TSD is activated when the junction temperature (Tj) reaches $175^{\circ}C$ (with $25^{\circ}C$ hysteresis), and the output terminal is switched to Hi-z. The TSD circuit aims to intercept IC from high temperature. The guarantee and protection of IC are not purpose. Therefore, please do not use this IC after TSD circuit operates, nor use it for assumption that operates the TSD circuit.

10. Inspection by the set circuit board

The stress might hang to IC by connecting the capacitor to the terminal with low impedance. Then, please discharge electricity in each and all process. Moreover, in the inspection process, please turn off the power before mounting the IC, and turn on after mounting the IC. In addition, please take into consideration the countermeasures for electrostatic damage, such as giving the earth in assembly process, transportation or preservation.

11. IC terminal input

This IC is a monolithic IC, and has P^+ isolation and P substrate for the element separation. Therefore, a parasitic PN junction is firmed in this P-layer and N-layer of each element. For instance, the resistor or the transistor is connected to the terminal as shown in the figure below. When the GND voltage potential is greater than the voltage potential at Terminals A or B, the PN junction operates as a parasitic diode. In addition, the parasitic NPN transistor is formed in said parasitic diode and the N layer of surrounding elements close to said parasitic diode. These parasitic elements are formed in the IC because of the voltage relation. The parasitic element operating causes the wrong operation and destruction. Therefore, please be careful so as not to operate the parasitic elements by impressing to input terminals lower voltage than GND(P substrate). Please do not apply the voltage to the input terminal when the power-supply voltage is not impressed. Moreover, please impress each input terminal lower than the power-supply voltage or equal to the specified range in the guaranteed voltage when the power-supply voltage is input terminal by impressing.



12. Earth wiring pattern

Use separate ground lines for control signals and high current power driver outputs. Because these high current outputs that flows to the wire impedance changes the GND voltage for control signal. Therefore, each ground terminal of IC must be connected at the one point on the set circuit board. As for GND of external parts, it is similar to the above-mentioned.

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